

TECHNIQUES FOR TRIPLE AND QUADRUPLE DAMASCENE FABRICATION

This application is a DIV of 69/165,233 10/01/1998 PAT 6,225,207 and

FIELD OF THE INVENTION

- The present invention relates to semiconductor device interconnect lines and via plugs
5 which are fabricated using damascene techniques.

BACKGROUND OF THE INVENTION

- A semiconductor device such as an IC (integrated circuit) generally has electronic
10 circuit elements such as transistors, diodes and resistors fabricated integrally on a single body
of semiconductor material. The various circuit elements are connected through conductive
connectors to form a complete circuit which can contain millions of individual circuit
elements. Advances in semiconductor materials and processing techniques have resulted in
reducing the overall size of the IC circuit elements while increasing their number on a single
15 body. Additional miniaturization is highly desirable for improved IC performance and cost
reduction. Interconnects provide the electrical connections between the various electronic
elements of an IC and they form the connections between these elements and the device's
external contact elements, such as pins, for connecting the IC to other circuits. Typically,
interconnect lines form horizontal connections between electronic circuit elements while
20 conductive via plugs form vertical connections between the electronic circuit elements,
resulting in layered connections.

- A variety of techniques are employed to create interconnect lines and via plugs. One
such technique involves a process generally referred to as dual damascene, which includes
25 forming a trench and an underlying via hole. The trench and the via hole are simultaneously
filled with a conductor material, for example a metal, thus simultaneously forming an
interconnect line and an underlying via plug. Examples of conventional dual damascene
fabrication techniques are disclosed in Kaanta et al., "Dual Damascene: A ULSI Wiring
Technology", Jun. 11-12, 1991, VMIC Conference, IEEE, pages 144-152 and in U.S. Pat. No.
30 5,635,423 to Huang et al., 1997.

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